MPS2222A is a Preferred Device

General Purpose Transistors

NPN Silicon

Features

• Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage MPS2222 MPS2222A	V _{CEO}	30 40	Vdc
Collector-Base Voltage MPS2222 MPS2222A	V _{CBO}	60 75	Vdc
Emitter-Base Voltage MPS2222 MPS2222A	V _{EBO}	5.0 6.0	Vdc
Collector Current – Continuous	I _C	600	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

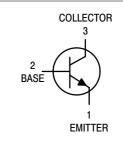
THERMAL CHARACTERISTICS

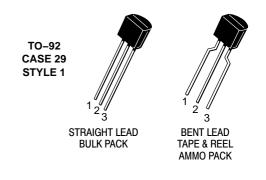
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

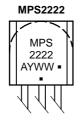
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MARKING DIAGRAMS





A = Assembly Location

Y = Year

WW = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

ON

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (I _C = 10 mAdc, I _B = 0)	MPS2222 MPS2222A	V _{(BR)CEO}	30 40	_ _	Vdc
Collector – Base Breakdown Voltage $(I_C = 10 \mu Adc, I_E = 0)$	MPS2222 MPS2222A	V _{(BR)CBO}	60 75	_ _	Vdc
Emitter – Base Breakdown Voltage $(I_E = 10 \mu Adc, I_C = 0)$	MPS2222 MPS2222A	$V_{(BR)EBO}$	5.0 6.0	_ _	Vdc
Collector Cutoff Current (V _{CE} = 60 Vdc, V _{EB(off)} = 3.0 Vdc)	MPS2222A	I _{CEX}	-	10	nAdc
Collector Cutoff Current $(V_{CB} = 50 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 60 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 60 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 50 \text{ Vdc}, I_E = 0, T_A = 125^{\circ}\text{C})$ $(V_{CB} = 50 \text{ Vdc}, I_E = 0, T_A = 125^{\circ}\text{C})$	MPS2222 MPS2222A MPS2222 MPS2222A	I _{CBO}	- - - -	0.01 0.01 10 10	μAdc
Emitter Cutoff Current (V _{EB} = 3.0 Vdc, I _C = 0)	MPS2222A	I _{EBO}	_	100	nAdc
Base Cutoff Current (V _{CE} = 60 Vdc, V _{EB(off)} = 3.0 Vdc)	MPS2222A	I _{BL}	-	20	nAdc
ON CHARACTERISTICS	_				
DC Current Gain $ \begin{array}{l} (I_C=0.1 \text{ mAdc, } V_{CE}=10 \text{ Vdc}) \\ (I_C=1.0 \text{ mAdc, } V_{CE}=10 \text{ Vdc}) \\ (I_C=1.0 \text{ mAdc, } V_{CE}=10 \text{ Vdc}) \\ (I_C=10 \text{ mAdc, } V_{CE}=10 \text{ Vdc}, T_A=-55^{\circ}C) \\ (I_C=150 \text{ mAdc, } V_{CE}=10 \text{ Vdc}) \text{ (Note 1)} \\ (I_C=150 \text{ mAdc, } V_{CE}=1.0 \text{ Vdc}) \text{ (Note 1)} \\ (I_C=500 \text{ mAdc, } V_{CE}=1.0 \text{ Vdc}) \text{ (Note 1)} \\ \end{array} $	MPS2222A only MPS2222 MPS2222A	h _{FE}	35 50 75 35 100 50 30 40	- - - 300 - -	-
Collector – Emitter Saturation Voltage (Note 1) ($I_C = 150 \text{ mAdc}$, $I_B = 15 \text{ mAdc}$) ($I_C = 500 \text{ mAdc}$, $I_B = 50 \text{ mAdc}$)	MPS2222 MPS2222A MPS2222 MPS2222A	V _{CE(sat)}	- - - -	0.4 0.3 1.6 1.0	Vdc
Base – Emitter Saturation Voltage (Note 1) $(I_C = 150 \text{ mAdc}, I_B = 15 \text{ mAdc})$ $(I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc})$	MPS2222 MPS2222A MPS2222 MPS2222A	V _{BE(sat)}	_ 0.6 _ _	1.3 1.2 2.6 2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product (Note 2) (I _C = 20 mAdc, V _{CE} = 20 Vdc, f = 100 MHz)	MPS2222 MPS2222A	f _T	250 300	_ _	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz)		C _{obo}	_	8.0	pF
Input Capacitance (V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz)	MPS2222 MPS2222A	C _{ibo}	_ _	30 25	pF
Input Impedance ($I_C = 1.0 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$) ($I_C = 10 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)	MPS2222A MPS2222A	h _{ie}	2.0 0.25	8.0 1.25	kΩ
Voltage Feedback Ratio ($I_C = 1.0 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$) ($I_C = 10 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)	MPS2222A MPS2222A	h _{re}	_ _	8.0 4.0	X 10 ⁻⁴
Small–Signal Current Gain ($I_C = 1.0 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$) ($I_C = 10 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)	MPS2222A MPS2222A	h _{fe}	50 75	300 375	-
Output Admittance ($I_C = 1.0 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$) ($I_C = 10 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)	MPS2222A MPS2222A	h _{oe}	5.0 25	35 200	μmhos
Collector Base Time Constant (I _E = 20 mAdc, V _{CB} = 20 Vdc, f = 31.8 MHz)	MPS2222A	rb′C _c	_	150	ps
Noise Figure (I _C = 100 μ Adc, V _{CE} = 10 Vdc, R _S = 1.0 k Ω , f = 1.0 kHz)	MPS2222A	NF	_	4.0	dB

^{1.} Pulse Test: Pulse Width $\leq 300~\mu s$, Duty Cycle $\leq 2\%$. 2. f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted) (Continued)

Characteristic			Min	Max	Unit
SWITCHING CHARACTERISTICS MPS2222A only					
Delay Time	$(V_{CC} = 30 \text{ Vdc}, V_{BE(off)} = -0.5 \text{ Vdc},$	t _d	-	10	ns
Rise Time	I _C = 150 mAdc, I _{B1} = 15 mAdc) (Figure 1)	t _r	-	25	ns
Storage Time	(V _{CC} = 30 Vdc, I _C = 150 mAdc,	ts	-	225	ns
Fall Time	$I_{B1} = I_{B2} = 15 \text{ mAdc}$ (Figure 2)	t _f	-	60	ns

SWITCHING TIME EQUIVALENT TEST CIRCUITS

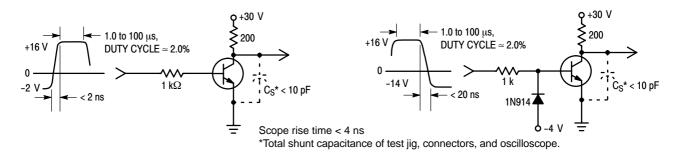


Figure 1. Turn-On Time

Figure 2. Turn-Off Time

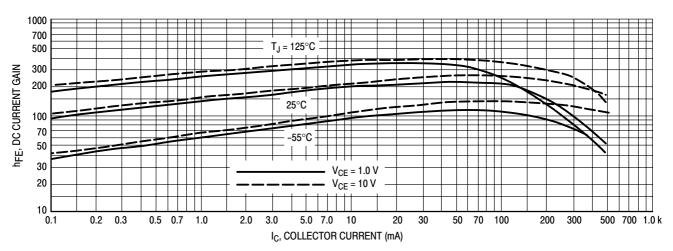


Figure 3. DC Current Gain

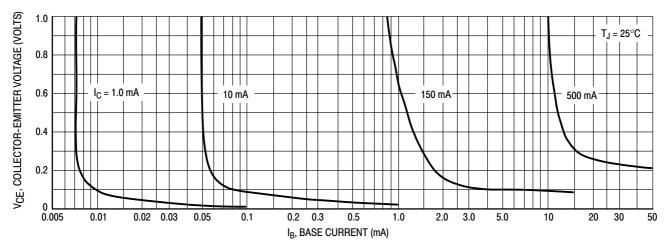


Figure 4. Collector Saturation Region

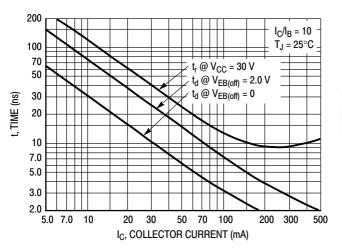


Figure 5. Turn - On Time

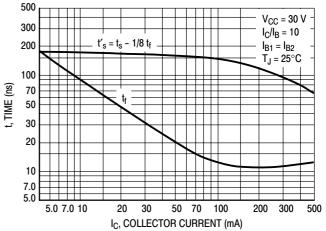


Figure 6. Turn - Off Time

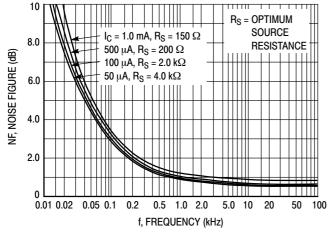


Figure 7. Frequency Effects

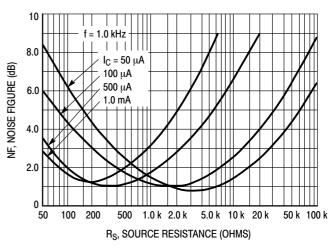
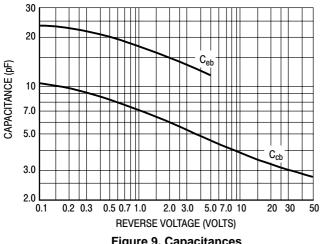


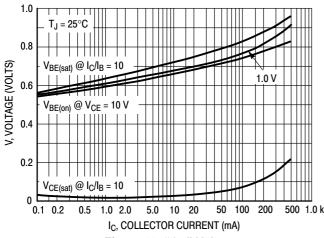
Figure 8. Source Resistance Effects



f_T, CURRENT-GAIN BANDWIDTH PRODUCT (MHz) 500 V_{CE} = 20 V $T_J = 25^{\circ}C$ 300 200 100 70 50 **∟** 1.0 5.0 7.0 10 70 100 I_C, COLLECTOR CURRENT (mA)

Figure 9. Capacitances

Figure 10. Current-Gain Bandwidth Product



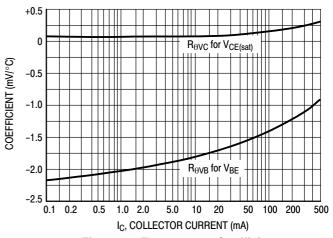


Figure 11. "On" Voltages

Figure 12. Temperature Coefficients

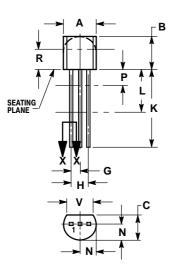
ORDERING INFORMATION

Device	Package	Shipping [†]
MPS2222G	TO-92 (Pb-Free)	5000 Units / Bulk
MPS2222RLRP	TO-92	2000 / Tape & Ammo Box
MPS2222RLRPG	TO-92 (Pb-Free)	2000 / Tape & Ammo Box
MPS2222A	TO-92	5000 Units / Bulk
MPS2222AG	TO-92 (Pb-Free)	5000 Units / Bulk
MPS2222ARLG	TO-92 (Pb-Free)	2000 / Tape & Reel
MPS2222ARLRA	TO-92	2000 / Tape & Reel
MPS2222ARLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel
MPS2222ARLRMG	TO-92 (Pb-Free)	2000 / Tape & Reel
MPS2222ARLRPG	TO-92 (Pb-Free)	2000 / Tape & Ammo Box

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 ISSUE AM



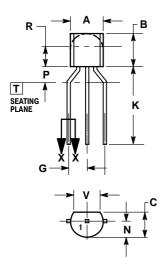
STRAIGHT LEAD **BULK PACK**



NOTES

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
 CONTOUR OF PACKAGE BEYOND DIMENSION R
- IS UNCONTROLLED.
 LEAD DIMENSION IS UNCONTROLLED IN P AND
 BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIM	ETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	



BENT LEAD TAPE & REEL AMMO PACK



- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS.
- CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM

	MILLIMETERS		
DIM	MIN MAX		
Α	4.45	5.20	
В	4.32	5.33	
С	3.18	4.19	
D	0.40	0.54	
G	2.40	2.80	
J	0.39	0.50	
K	12.70		
N	2.04	2.66	
P	1.50	4.00	
R	2.93		
V	3 //3		

STYLE 1:

PIN 1. EMITTER

BASE

COLLECTOR

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